

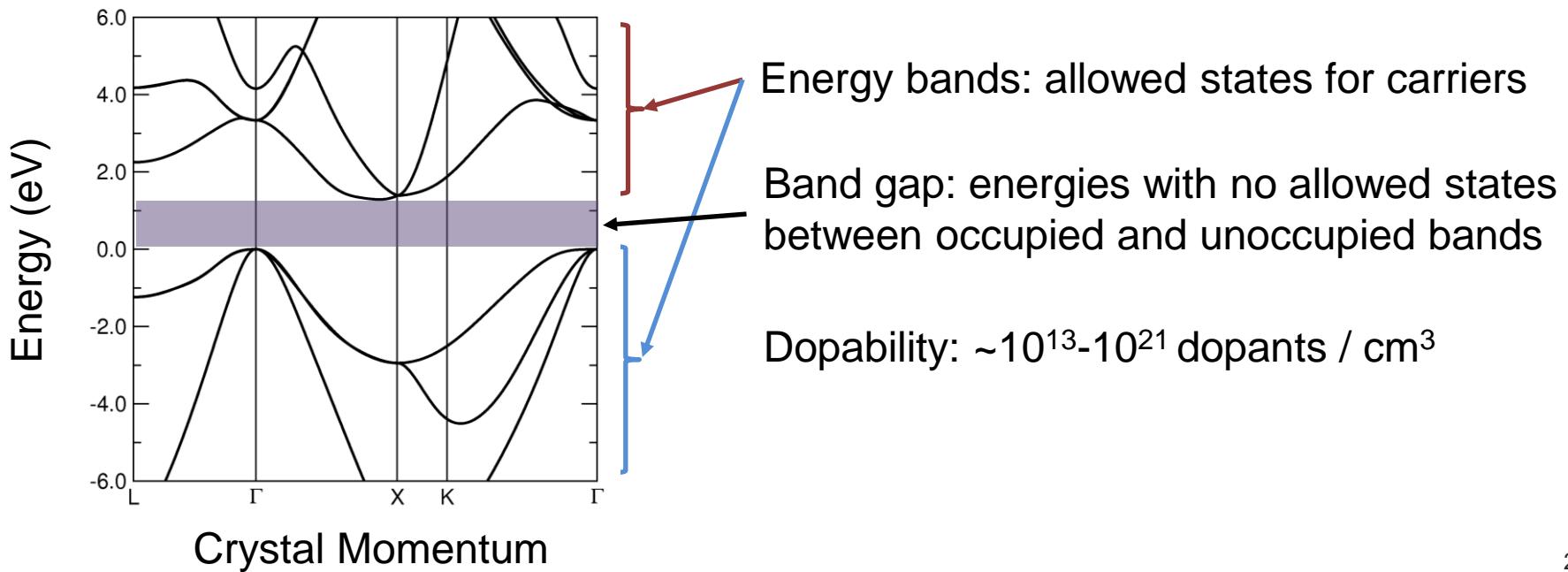


# Studying Direct and Phonon-assisted Quantum Processes in Semiconductors

DOE CSGF Annual Review  
July 18<sup>th</sup>, 2023

# Deconstructing the Title

## Studying Direct and Phonon-assisted Quantum Processes in Semiconductors

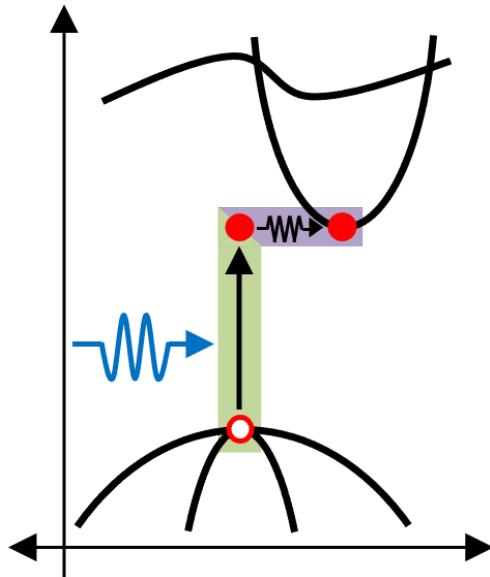
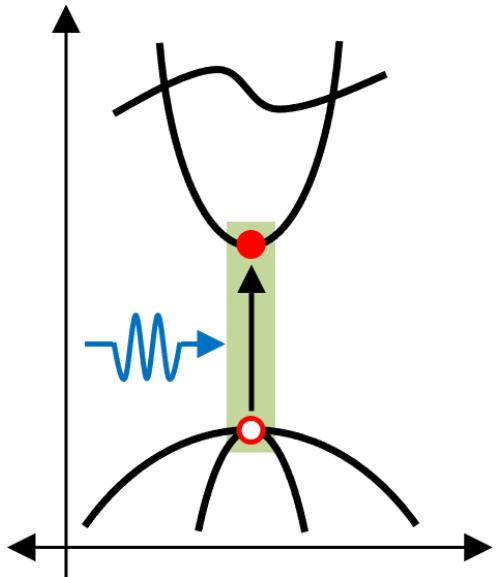


# Deconstructing the Title



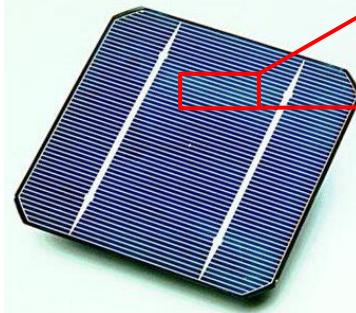
## Studying Direct and Phonon-assisted Quantum Processes in Semiconductors

Direct  
1-step  
Transition between initial and final state  
Energy and momentum conservation

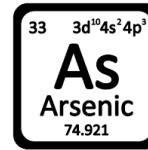
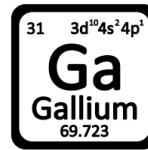


Phonon-assisted  
2-step  
Includes “virtual” transition with an intermediate state  
Momentum conservation relaxed

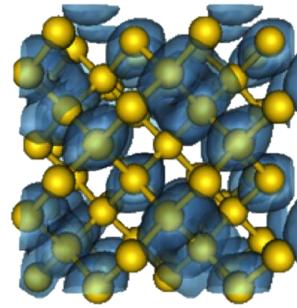
# From Macroscopic to Microscopic



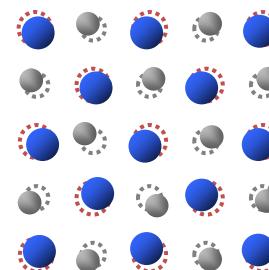
Devices



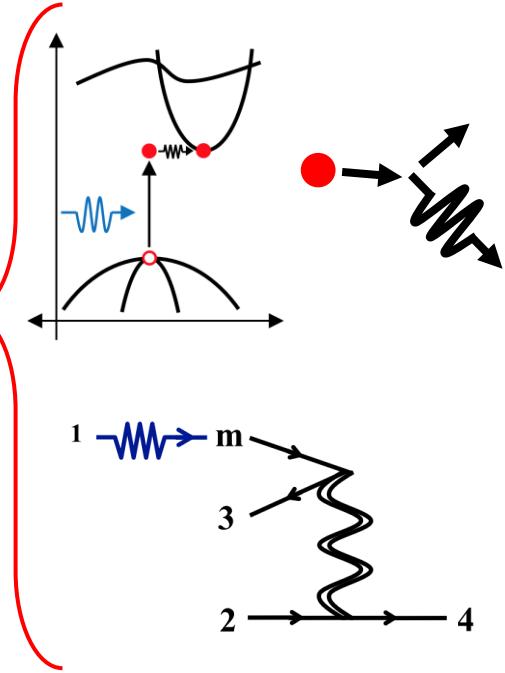
Materials



$$\left( -\frac{\hbar^2}{2m} \nabla^2 + v_{KS}(\mathbf{r}) \right) \varphi(\mathbf{r}) = \epsilon \varphi(\mathbf{r})$$

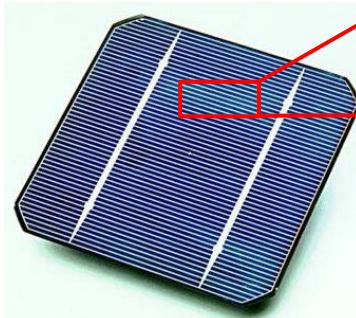


Electronic Structure

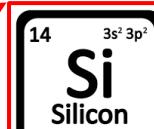
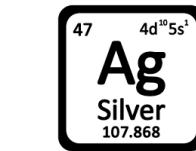


Quantum Processes

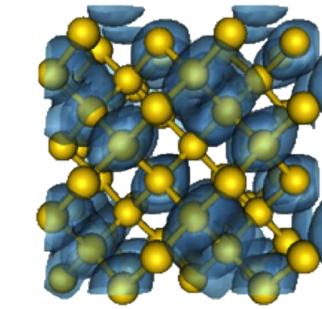
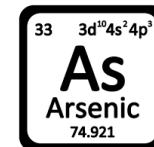
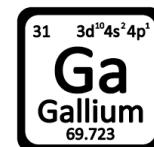
# From Macroscopic to Microscopic



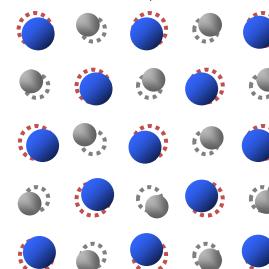
Devices



Semiconductors



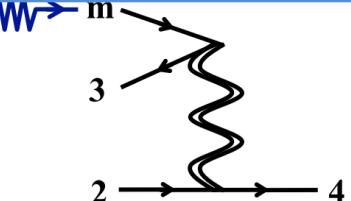
$$-\frac{\hbar^2}{2m} \nabla^2 + v_{KS}(\mathbf{r}) \Big) \varphi(\mathbf{r}) = \epsilon \varphi(\mathbf{r})$$



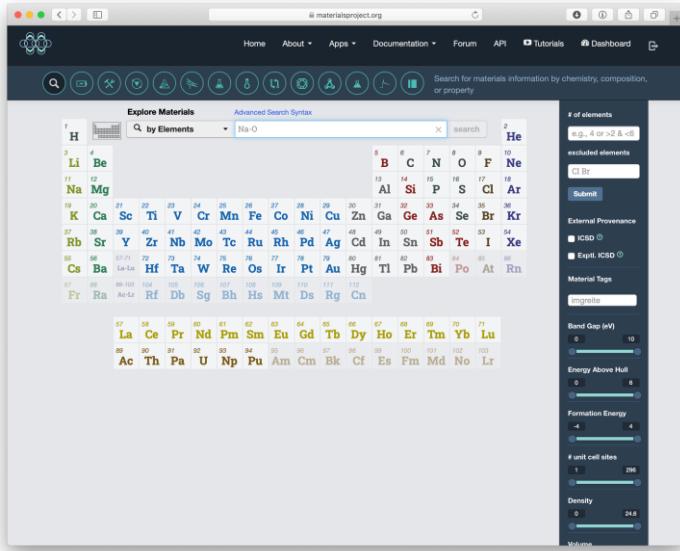
Materials

Electronic Structure

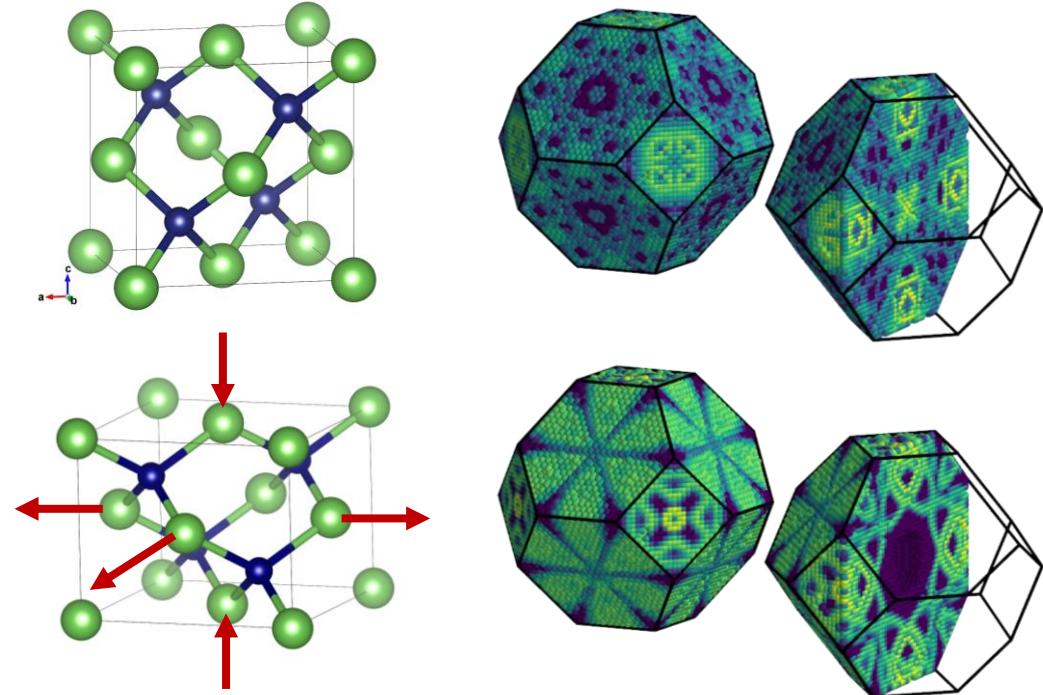
Direct and  
Phonon-assisted  
Quantum Processes



# The Benefit of Computation

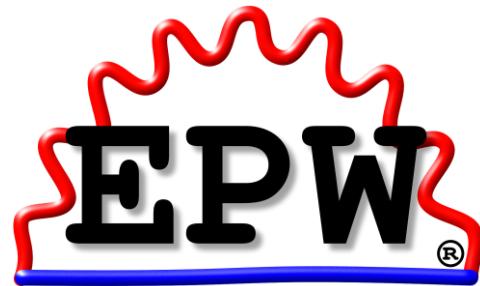


materialsproject.org



Computational methods can accelerate discovery and improve our understanding of the physics underlying material properties

# Computational Toolbox



WANNIER90



BerkeleyGW

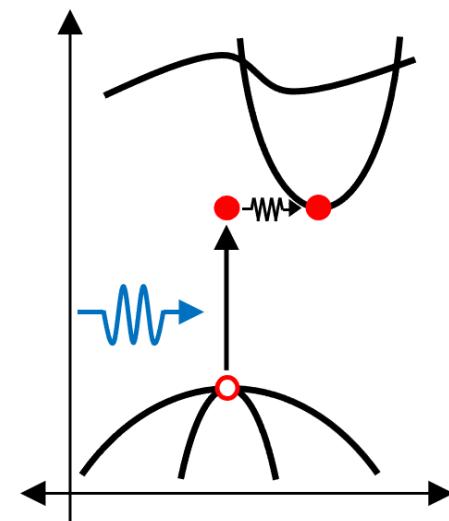
In-house  
Auger-Meitner  
Code\*

\*name to be determined!

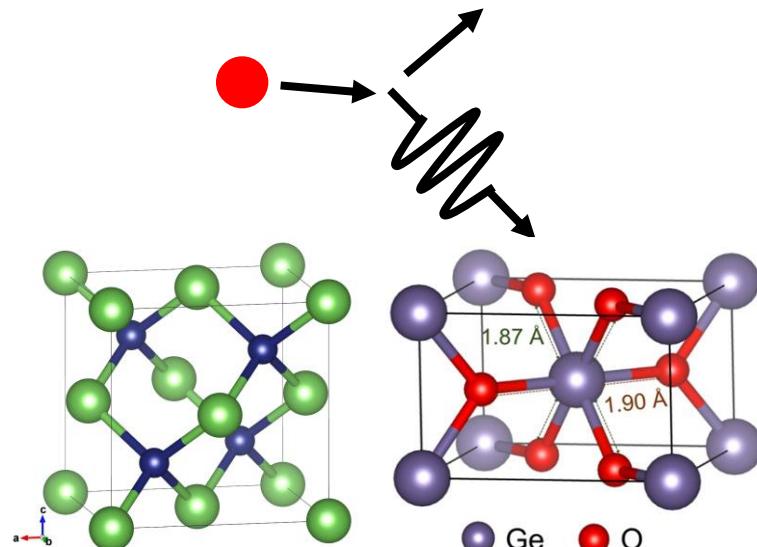
# A Diverse Array of Quantum Processes



Optical absorption  
in boron arsenide



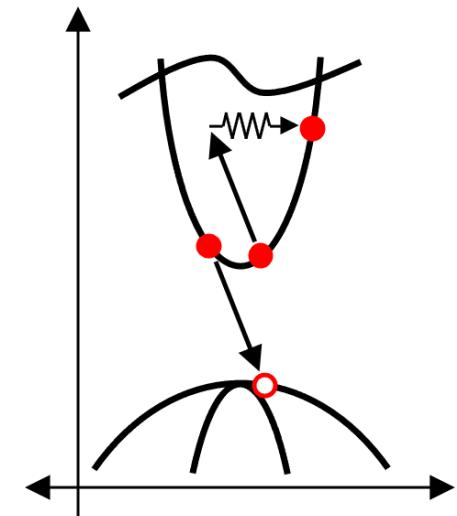
Carrier mobility in boron arsenide  
and rutile germanium dioxide



K. Bushick et al., Appl. Phys. Lett. 114, 022101 (2019)  
B. Song, K. Chen, K. Bushick et al., Appl. Phys. Lett. 116, 141903 (2020)

K. Bushick et al., npj Comput. Mater. 6, 3 (2020)  
K. Bushick et al., Appl. Phys. Lett. 117, 182104 (2020)

Auger-Meitner  
recombination in silicon



K. Bushick and E. Kioupakis, Phys. Rev. Lett. Accepted, (2023)

# Auger-Meitner: A Note on Naming



PHYSICS TODAY

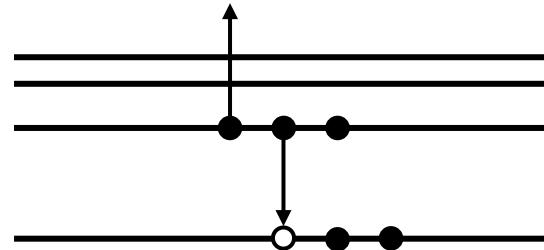
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Home > September 2019 (Volume 72, Issue 9) > Page 10, doi:10.1063/PT.3.4281

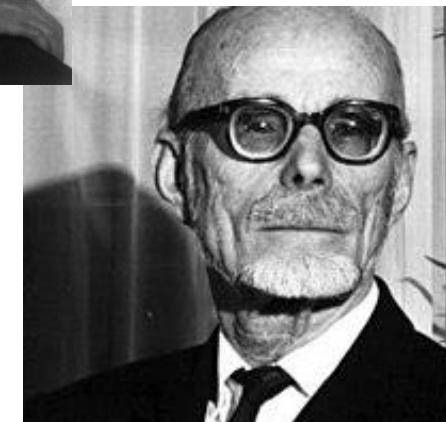
## A renaming proposal: “The Auger-Meitner effect”

Demetrios Matsakis  
(dnmyleasou@yahoo.com) Masterclock, Inc, Washington, DC

Anthea Coster  
Massachusetts Institute of Technology Haystack Observatory, Westford  
Brenda Laster  
Ben-Gurion University, Beer Sheba, Israel  
Ruth Sime  
Sacramento City College, Sacramento, California



Lise Meitner



Pierre Auger

D. Matsakis, et al., Phys. Today 72, 10 (2019)

[https://www.sciencehistory.org/sites/default/files/styles/rte\\_full\\_width/public/meitner\\_lise\\_courtesy\\_anne\\_meitner.jpg](https://www.sciencehistory.org/sites/default/files/styles/rte_full_width/public/meitner_lise_courtesy_anne_meitner.jpg)

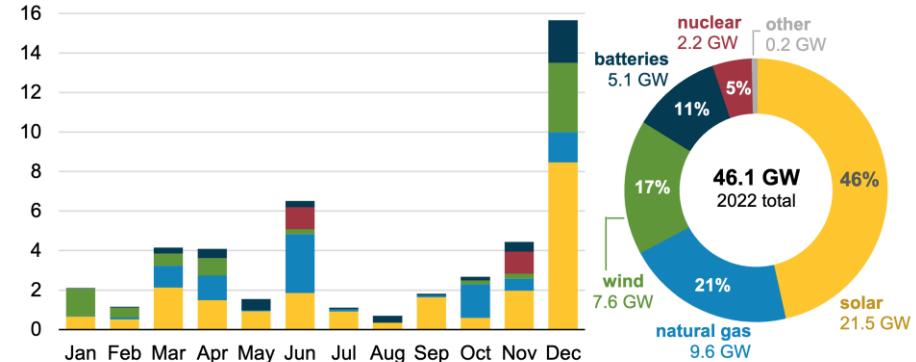
[https://upload.wikimedia.org/wikipedia/en/thumb/8/85/Pierre\\_Victor\\_Auger.jpg/200px-Pierre\\_Victor\\_Auger.jpg](https://upload.wikimedia.org/wikipedia/en/thumb/8/85/Pierre_Victor_Auger.jpg/200px-Pierre_Victor_Auger.jpg)



# Importance of Solar Cells

Planned U.S. utility-scale electric generating capacity additions (2022)

gigawatts (GW)



eia

$$\tau = \frac{n}{An + Bn^2 + Cn^3}$$

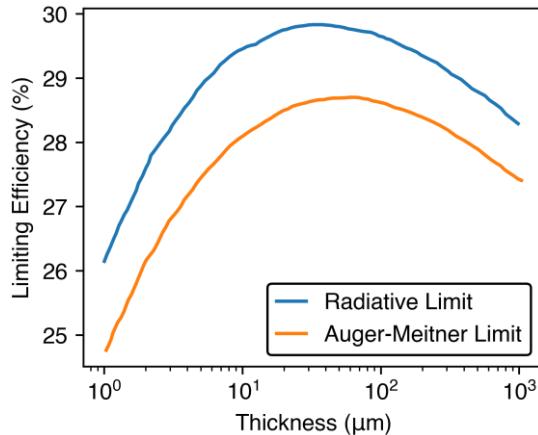
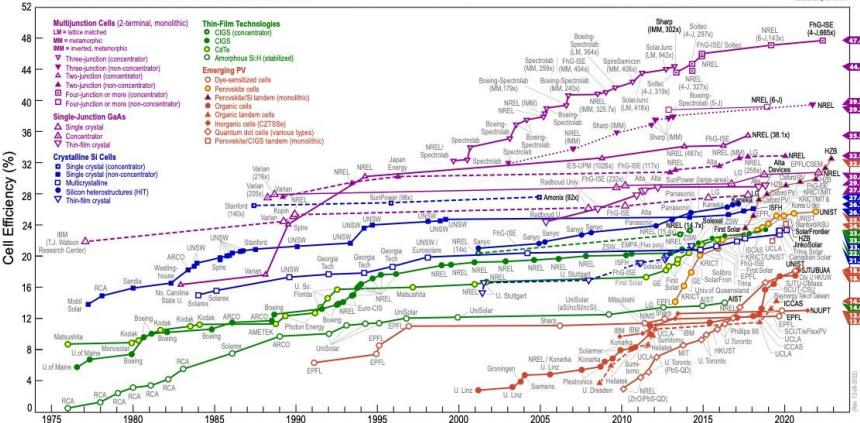
Diagram illustrating the relationship between energy and different recombination mechanisms:

- SRH:** Shockley-Read-Hall recombination occurs between conduction bands and valence bands.
- Radiative:** Radiative recombination occurs between valence bands.
- Auger-Meitner:** Auger-Meitner recombination occurs between conduction bands.

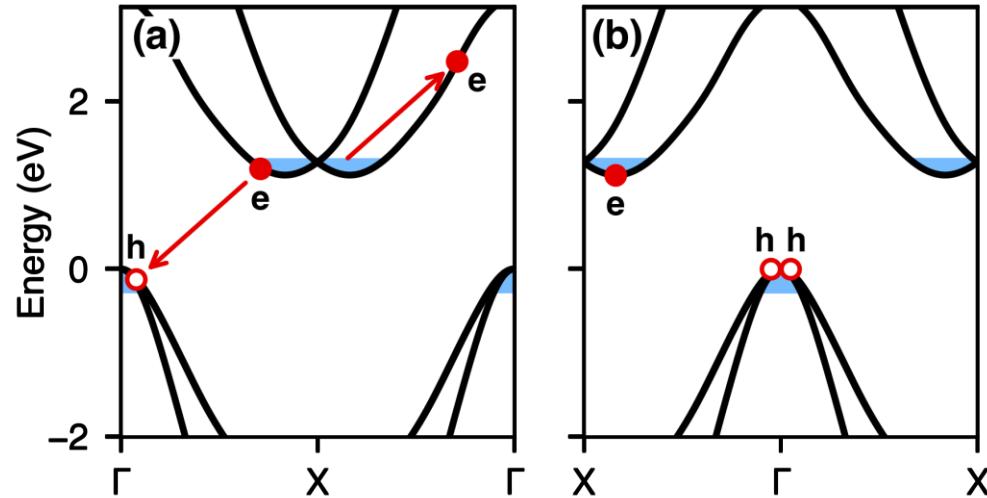
Below the diagram, the coefficients for the equation are shown:

- $R = An$
- $R = Bn^2$
- $R = Cn^3$

Best Research-Cell Efficiencies



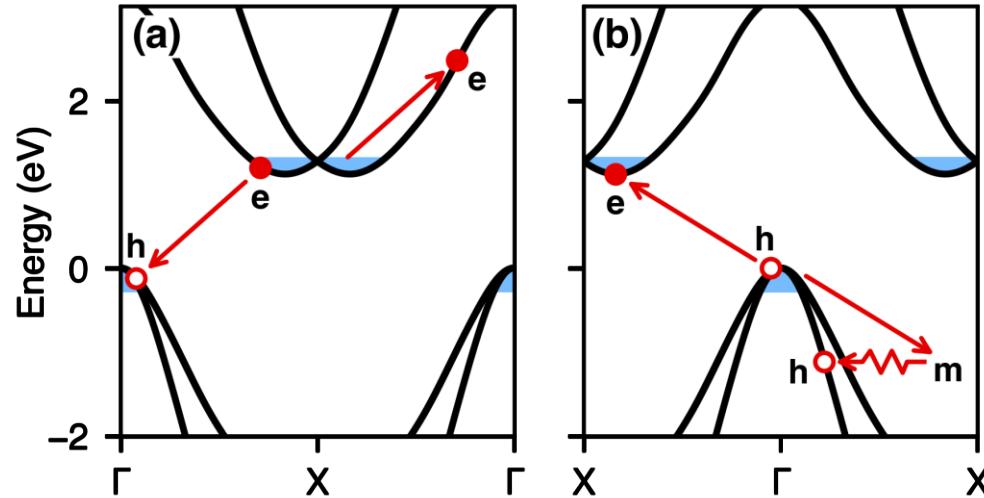
# Auger-Meitner Recombination



This recombination process involves three carriers near the band edges:  
either two electrons and a hole (eeh) or two holes and an electron (hhe)

We study two types of Auger-Meitner recombination:  
the (a) direct process and (b) phonon-assisted process

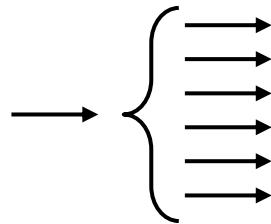
# Auger-Meitner Recombination



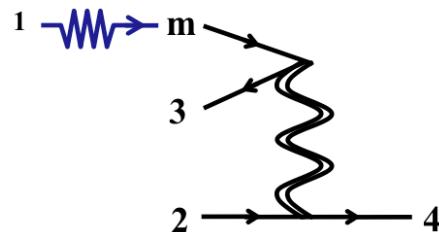
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We study two types of Auger-Meitner recombination:  
the (a) direct process and (b) phonon-assisted process

# Methodology + Code Development



Increased parallelism



Rewrote and generalized  
the phonon-assisted code

$$\delta(\epsilon_1 + \dots \mp \hbar\omega_{vq})$$

Added explicit energy  
conservation constraints

verbosity = 1 (valley)  
verbosity = 2 (band)  
verbosity = 3 (phonon)  
verbosity = 4 (k4)  
verbosity = 5 (p\_mag)

Added different verbose  
modes for analysis

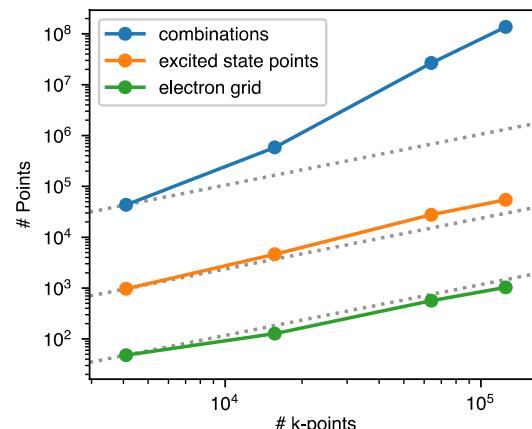


**GNUparallel**

Leverage processor parallelism  
for serial executables

**MPI-IO**

Parallelized IO, binary data



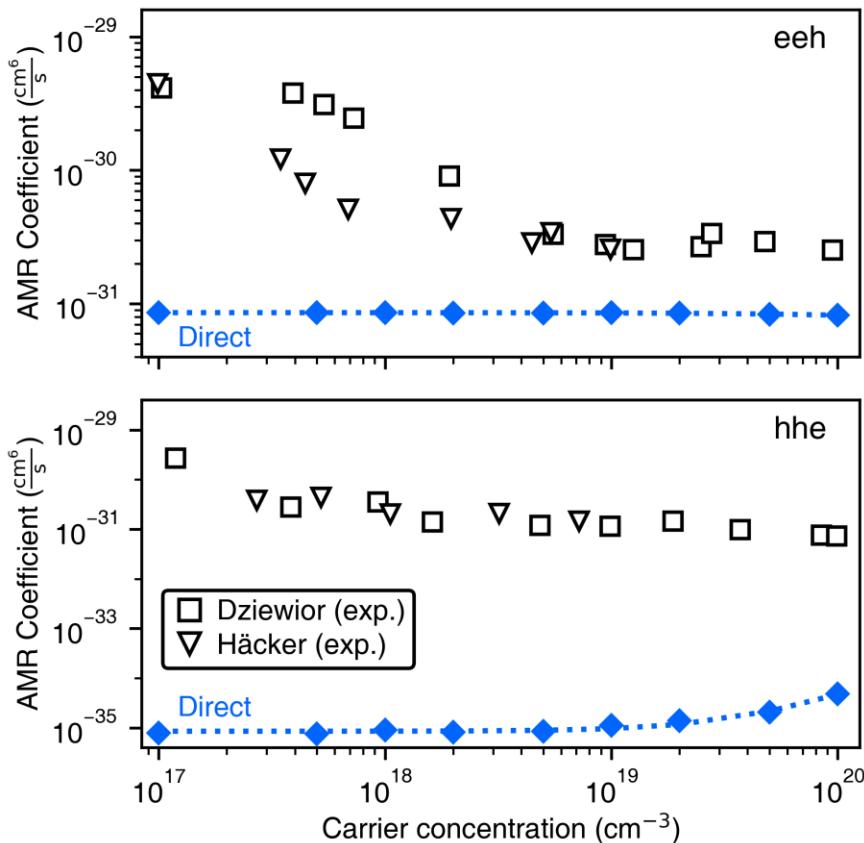
A direct run evaluates:  
100,000 wavefunctions (>1 TB)  
200,000,000  $M_{1234}$  terms

A phonon-assisted run evaluates:  
300,000 wavefunctions (>4 TB)  
150,000,000  $\tilde{M}_{1234;vq}$  terms

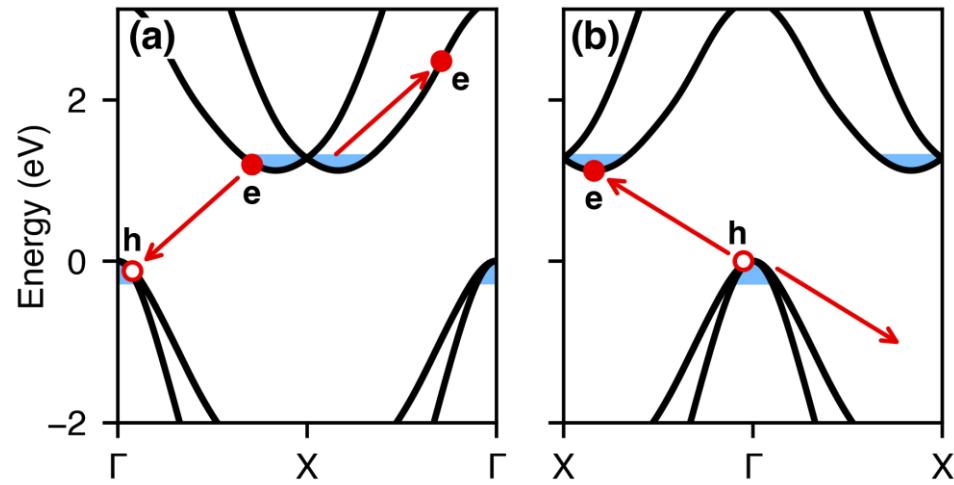
# AMR vs Carrier Concentration



K. Bushick and E. Kioupakis, Phys. Rev. Lett. Accepted, (2023)



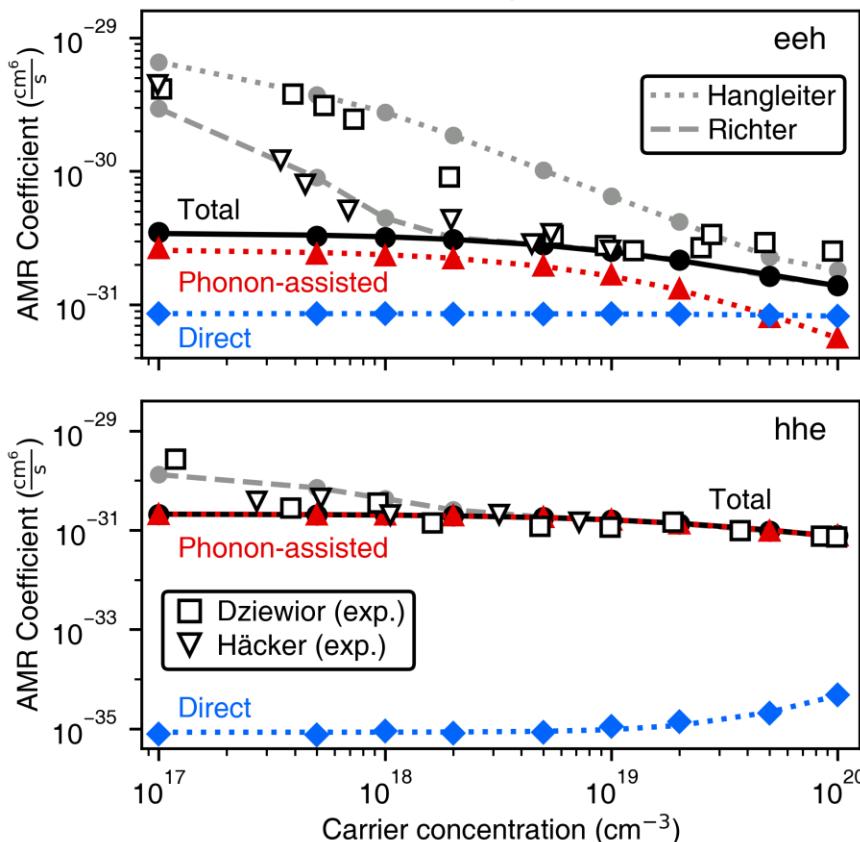
A. Hangleiter and R. Häcker, Phys. Rev. Lett. 65, 215 (1990)  
A. Richter, et al., Phys. Rev. B. 86, 165202 (2012)  
J. Dziewior and W. Schmid, Appl. Phys. Lett. 31, 346 (1977)  
R. Häcker and A. Hangleiter, J. Appl. Phys. 75, 7570 (1994)



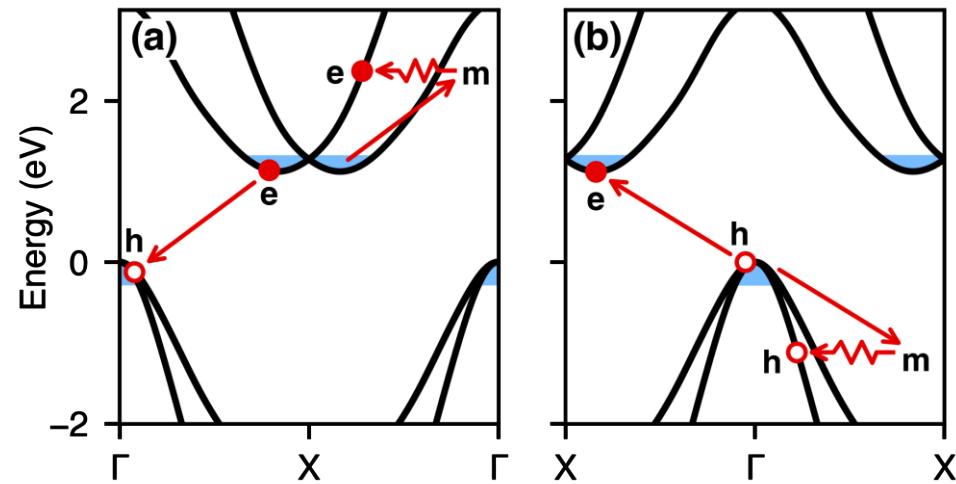
Phonon-assisted Auger-Meitner recombination must be considered not only for the hhe process, but also for the eeh process

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K. Bushick and E. Kioupakis, Phys. Rev. Lett. Accepted, (2023)



A. Hangleiter and R. Häcker, Phys. Rev. Lett. 65, 215 (1990)  
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Phonon-assisted Auger-Meitner recombination must be considered not only for the hhe process, but also for the eeh process



# Summary



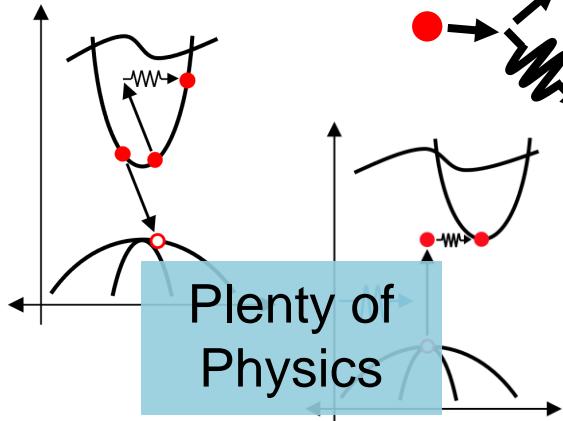
QUANTUM ESPRESSO

WANNIER90

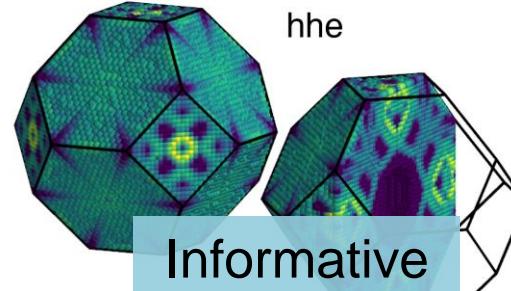
BerkeleyGW

In-house  
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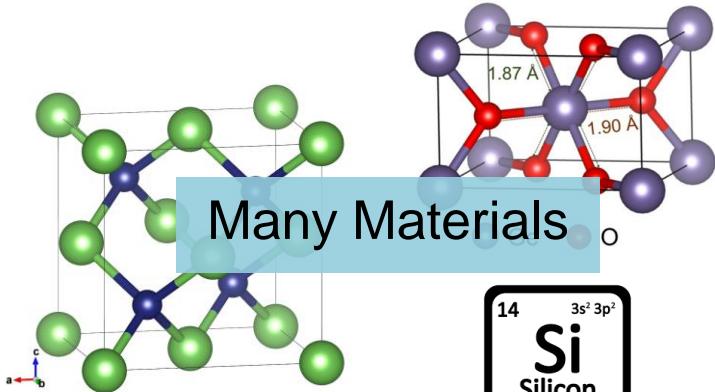
Tons of Tools



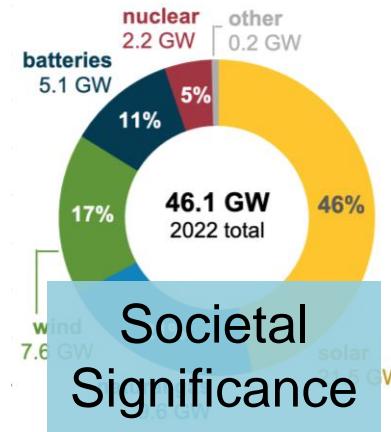
Plenty of Physics



Informative Insights



Many Materials



Societal Significance

# Acknowledgements

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- Prof. Emmanouil Kioupakis
- Kioupakis Research Group

MIT

- Prof. Gang Chen
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- Dr. Ke Chen

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- Prof. Feliciano Giustino (UT Austin)
- Dr. Hyungjun Lee (now EPFL)

LLNL (practicum)

- Dr. Brandon Wood
- Dr. Tim Hsu
- Dr. James Chapman (now Boston University)
- Dr. Kyoung Kweon

The entire Krell staff!



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